

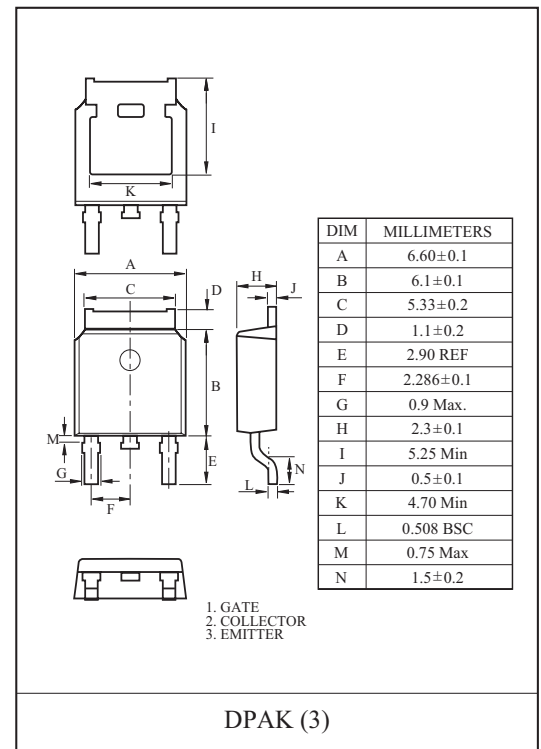
General Description

KEC Field Stop Trench IGBTs offer low switching losses, high energy efficiency and short circuit ruggedness.

It is designed for applications such as motor control, uninterrupted power.

FEATURES

- High speed switching
- High ruggedness, temperature stable behavior
- Short Circuit Withstand Times > 5 μ s(@T_C=100)
- Extremely enhanced avalanche capability



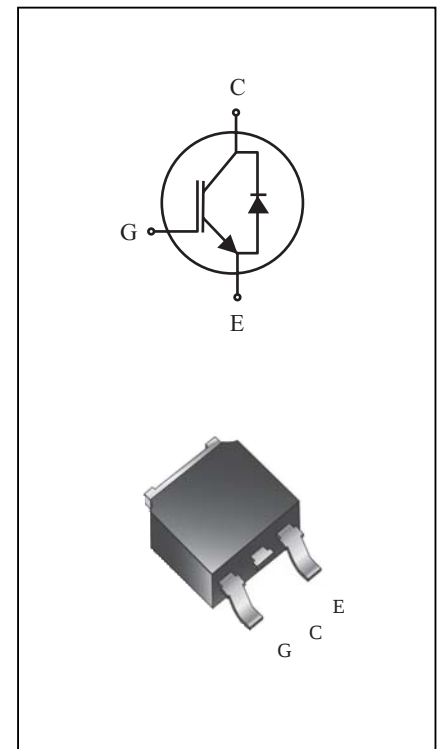
MAXIMUM RATING (Ta=25)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Emitter Voltage		V _{CES}	650	V
Gate-Emitter Voltage		V _{GES}	± 20	V
Collector Current	@T _C =25	I _C	30	A
	@T _C =100		15	A
Pulsed Collector Current		I _{CM} *	45	A
Diode Continuous Forward Current	@T _C =25	I _F	15	A
Diode Maximum Forward Current		I _{FM}	45	A
Maximum Power Dissipation	@T _C =25	P _D	99	W
	@T _C =100		39	W
Maximum Junction Temperature		T _j	150	
Storage Temperature Range		T _{stg}	-55 to + 150	

*Repetitive rating : Pulse width limited by max. junction temperature

THERMAL CHARACTERISTIC

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Junction to Case (IGBT)	R _{thJC}	1.26	/W
Thermal Resistance, Junction to Case (DIODE)	R _{thJC}	3.0	/W
Thermal Resistance, Junction to Ambient	R _{thJA}	62.5	/W



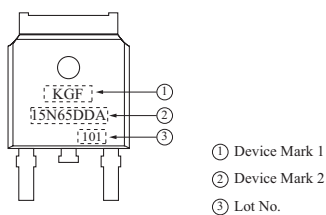
KGF15N65DDA

ELECTRICAL CHARACTERISTICS (Ta=25)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Static						
Collector-Emitter Brekdown Voltage	BV _{CES}	V _{GE} =0V, I _C =250 μA	650	-	-	V
Collector Cut-off Current	I _{CES}	V _{GE} =0V, V _{CE} =650V	-	-	250	μA
Gate Leakage Current	I _{GES}	V _{CE} =0V, V _{GE} = ± 20V	-	-	± 100	nA
Gate Threshold Voltage	V _{GE(th)}	V _{GE} =V _{CE} , I _C =2mA	3.9	4.9	5.9	V
Collector-Emitter Saturation Voltage	V _{CE(sat)}	V _{GE} =15V, I _C =15A	-	1.75	2.1	V
		V _{GE} =15V, I _C =30A, T _C = 25	-	2.34	-	V
		V _{GE} =15V, I _C =15A, T _C = 125	-	1.96	-	V
Dynamic						
Total Gate Charge	Q _g	V _{CC} =300V, V _{GE} =15V, I _C = 15A	-	29	-	nC
Gate-Emitter Charge	Q _{ge}		-	6.5	-	nC
Gate-Collector Charge	Q _{gc}		-	11.5	-	nC
Turn-On Delay Time	t _{d(on)}	V _{CC} =300V, I _C =15A, V _{GE} =15V, R _G =10 Ω Inductive Load, T _C = 25 (Note1)	-	21	-	ns
Rise Time	t _r		-	12	-	ns
Turn-Off Delay Time	t _{d(off)}		-	58	-	ns
Fall Time	t _f		-	14	-	ns
Turn-On Switching Loss	E _{on}		-	0.17	0.20	mJ
Turn-Off Switching Loss *Note(1)	E _{off}		-	0.07	0.09	mJ
Total Switching Loss	E _{ts}		-	0.24	0.29	mJ
Turn-On Delay Time	t _{d(on)}	V _{CC} =300V, I _C =15A, V _{GE} =15V, R _G =10 Ω Inductive Load, T _C = 125 (Note1)	-	21	-	ns
Rise Time	t _r		-	15	-	ns
Turn-Off Delay Time	t _{d(off)}		-	60	-	ns
Fall Time	t _f		-	23	-	ns
Turn-On Switching Loss	E _{on}		-	0.15	-	mJ
Turn-Off Switching Loss *Note(1)	E _{off}		-	0.14	-	mJ
Total Switching Loss	E _{ts}		-	0.29	-	mJ
Input Capacitance	C _{ies}	V _{CE} =30V, V _{GE} =0V, f=1MHz	-	827	992	pF
Ouput Capacitance	C _{oes}		-	54.75	-	pF
Reverse Transfer Capacitance	C _{res}		-	14.37	-	pF
Short Circuit Withstand Time	t _{sc}	V _{CC} =300V, V _{GE} =15V, T _C = 100	5	-	-	μs

* Note(1) : Energy loss include tail current and diode reverse recovery.

MARKING



KGF15N65DDA

ELECTRICAL CHARACTERISTICS OF DIODE

CHARACTERISTIC	SYMBOL	TEST CONDITION		MIN.	TYP.	MAX.	UNIT
Diode Forward Voltage	V _F	I _F =15A	T _C = 25	-	1.87	-	V
			T _C = 125	-	1.93	-	
Diode Reverse Recovery Time	t _{rr}	V _{CC} =300V, I _F =15A, di/dt=600A/ μs	T _C = 25	-	45	-	ns
			T _C = 125	-	59	-	
Diode Peak Reverse Recovery Current	I _{rr}		T _C = 25	-	12	-	A
			T _C = 125	-	11.3	-	
Diode Reverse Recovery Charge	Q _{rr}		T _C = 25	-	0.38	-	μC
			T _C = 125	-	0.54	-	

Fig 1. Saturation Voltage Characteristics

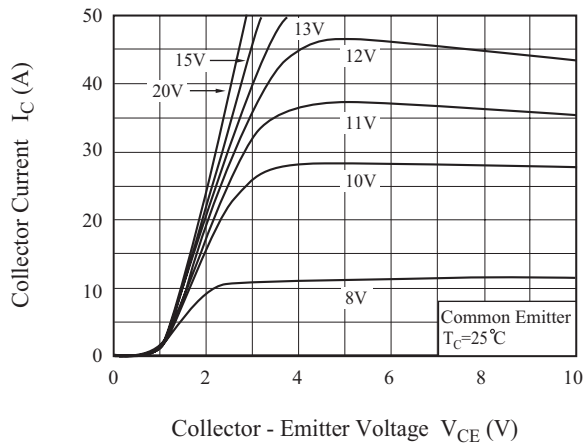


Fig 2. Saturation Voltage Characteristics

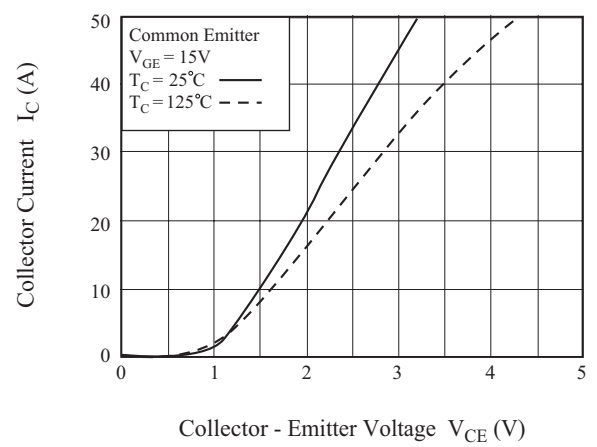


Fig 3. Saturation Voltage vs. Case Temperature

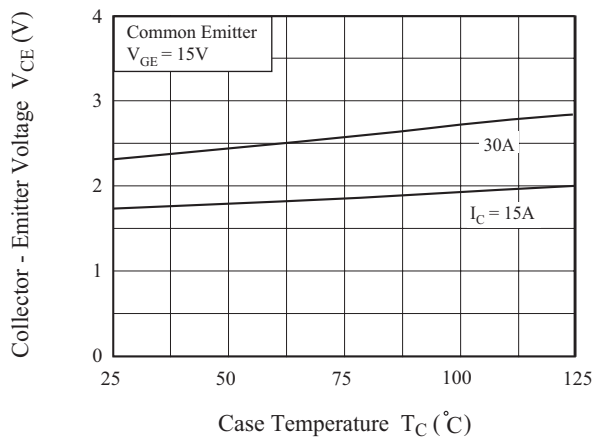


Fig 4. Saturation Voltage vs. V_{GE}

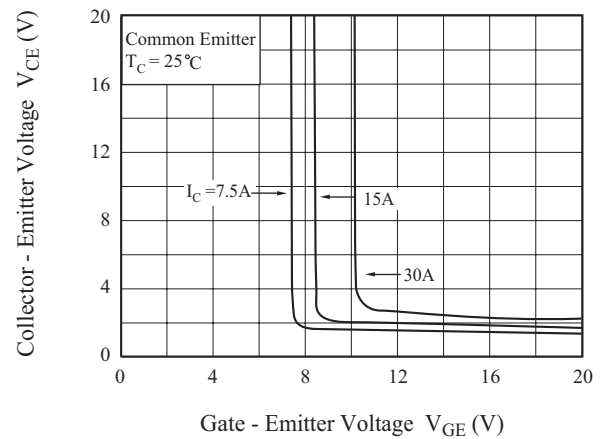


Fig 5. Saturation Voltage vs. V_{GE}

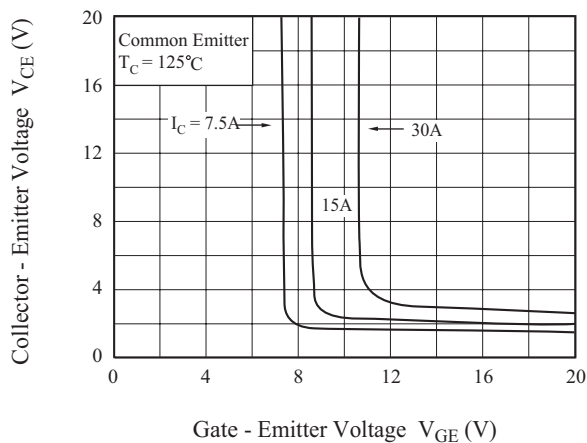


Fig 6. Capacitance Characteristics

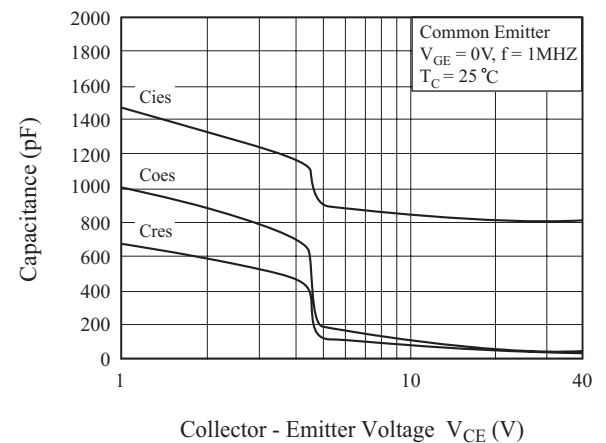


Fig 7. Turn-On Characteristics vs. Gate Resistance

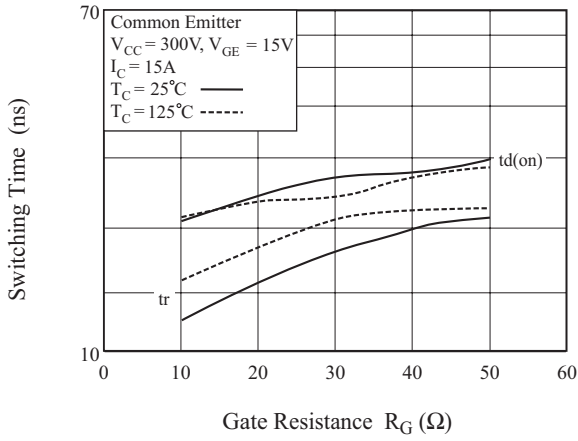


Fig 8. Turn-Off Characteristics vs. Gate Resistance

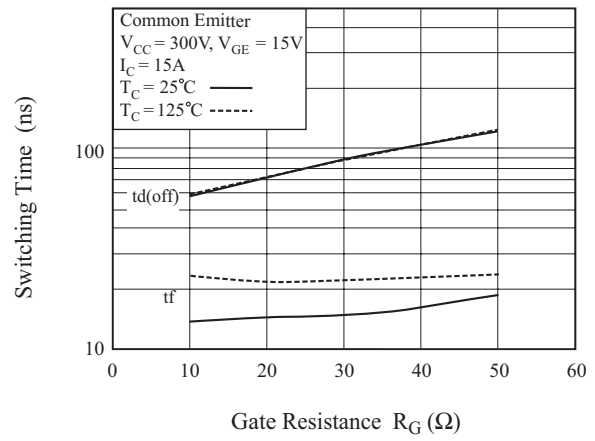


Fig 9. Switching Loss vs. Gate Resistance

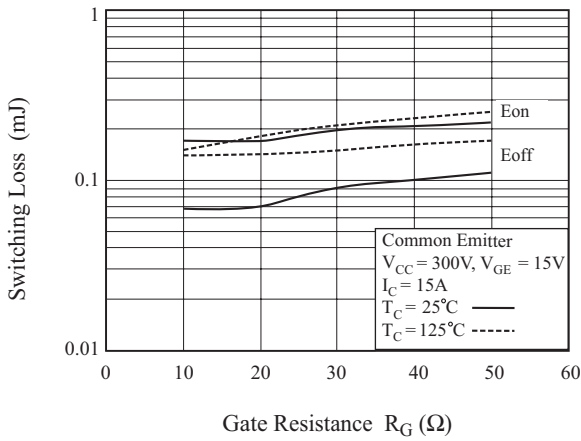


Fig 10. Turn-On Characteristics vs. Collector Current

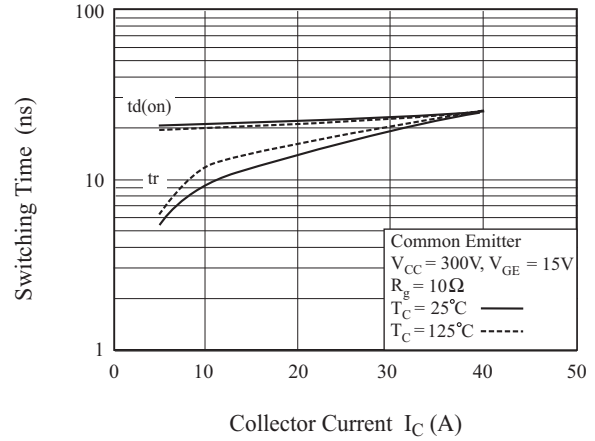


Fig 11. Turn-Off Characteristics vs. Collector Current

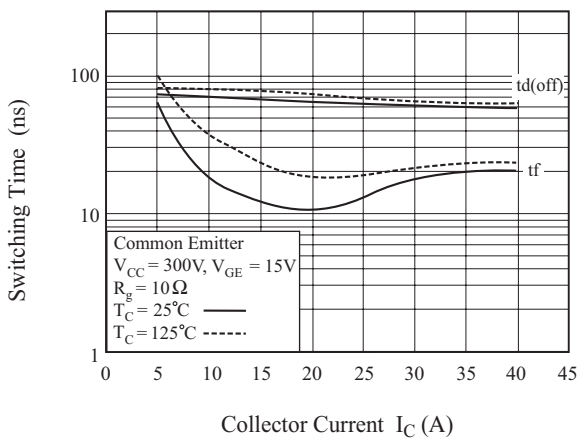


Fig 12. Switching Loss vs. Collector Current

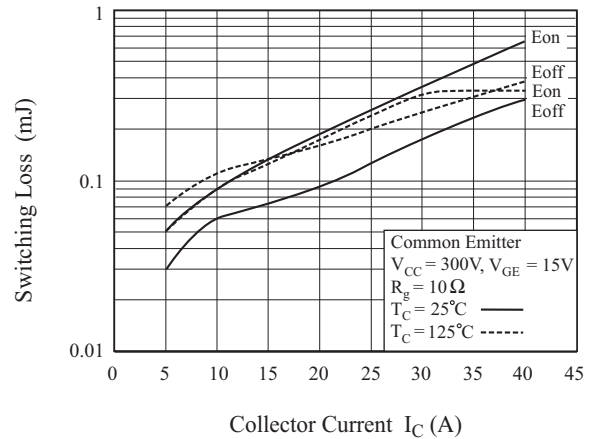


Fig 13. Gate Charge Characteristics

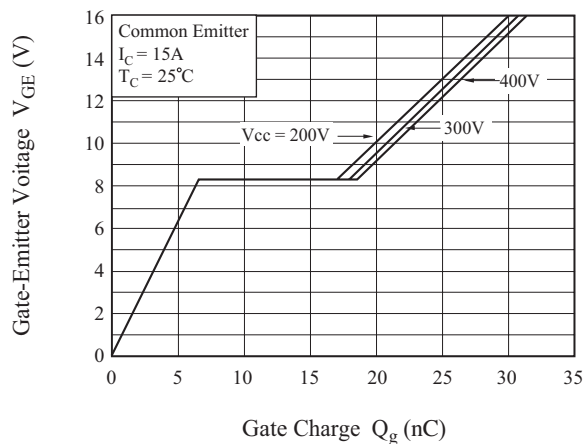


Fig 14. SOA Characteristics

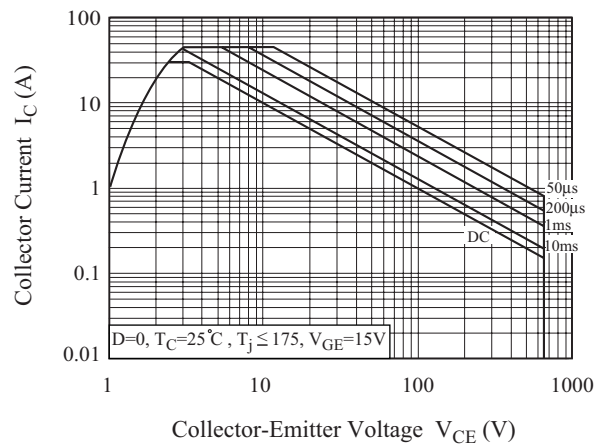


Fig 15. Turn-Off SOA

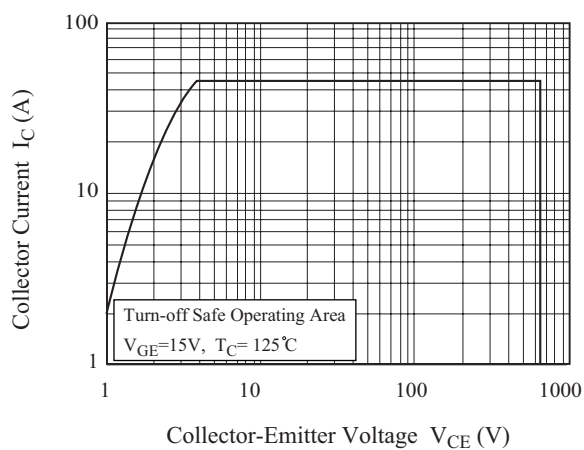


Fig 16. Transient Thermal Impedance of IGBT

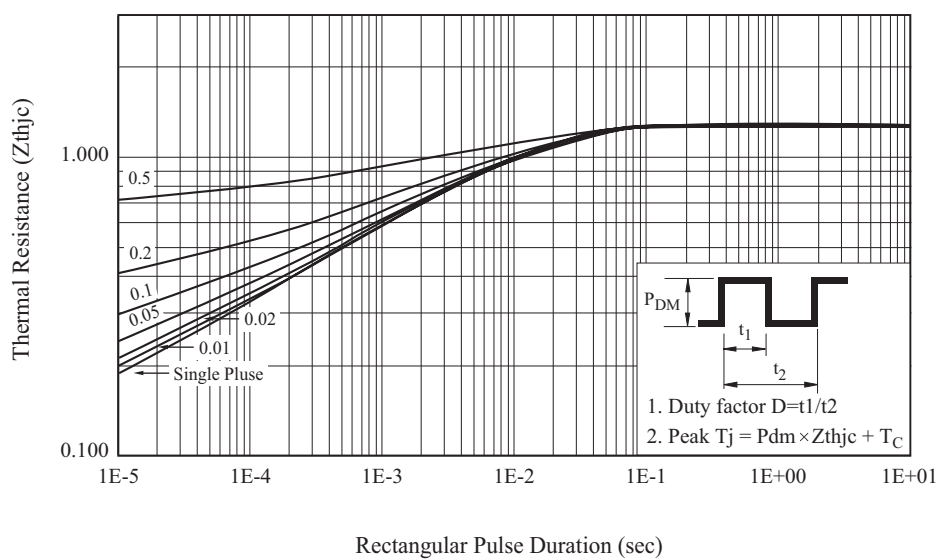


Fig 17. Forward Characteristics

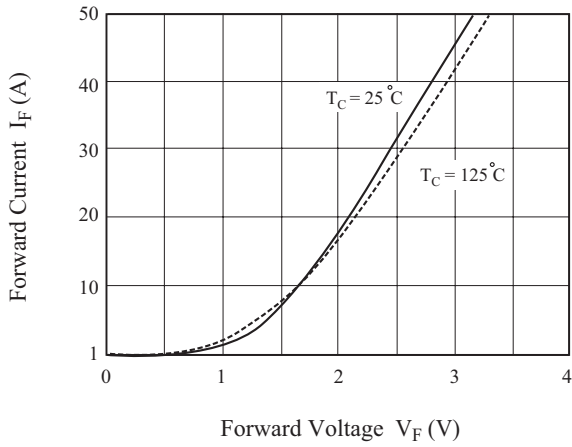


Fig 18. Reverse Recovery Current

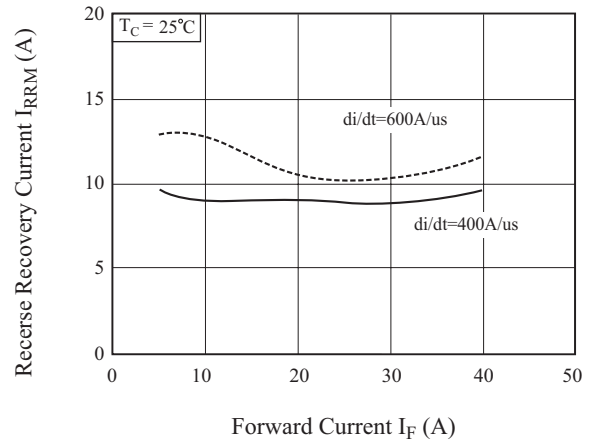


Fig 19. Reverse Recovery Time

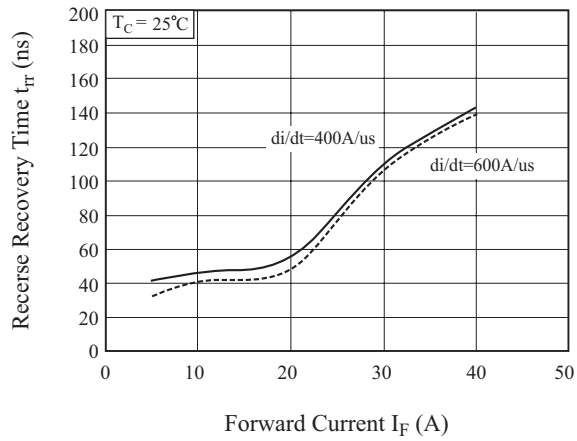


Fig 20. Switching Test Circuit

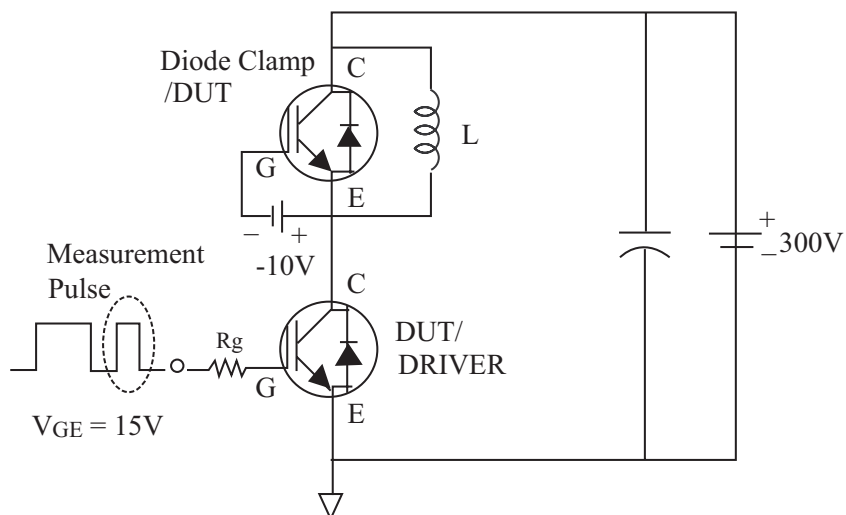


Fig 21. Definition Switching Time & Loss

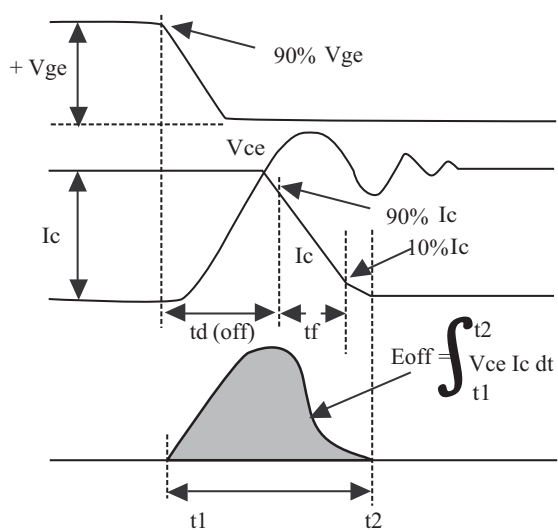
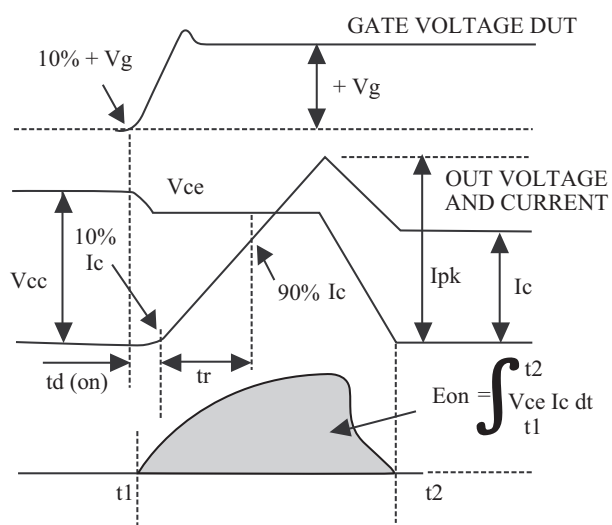


Fig 22. Definition Diode Switching Time

